

9097250 TOSHIBA (DISCRETE/OPTO)

SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

56C 07251 D T-33-21

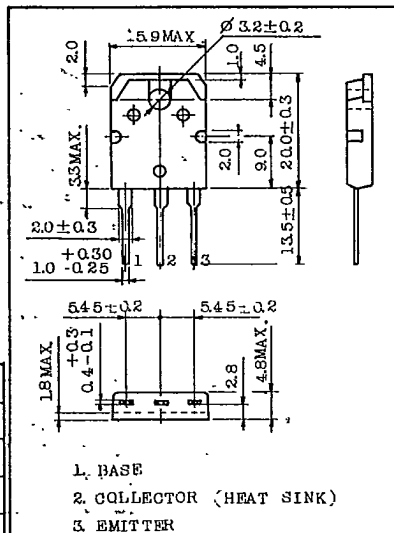
2SA1093

Unit in mm

AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS.

FEATURES:

- Complementary to 2SC2563.
- Recommended for 50W audio amplifier output stage.
- High transition frequency : $f_T=90\text{MHz(Typ.)}$



JEDEC	-
EIAJ	-
TOSHIBA	2-16B1A

Weight : 4.6g

MAXIMUM RATINGS (T_a=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-120	V
Collector-Emitter Voltage	V_{CE0}	-120	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-8	A
Base Current	I_B	-0.8	A
Collector Power Dissipation ($T_c=25^{\circ}\text{C}$)	P_C	80	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	V _{CB} =-120V, I _E =0	-	-	-50	μA
Emitter Cut-off Current	IEBO	VEB=-5V, I _C =0	-	-	-50	μA
Collector-Emitter Breakdown Voltage	V(BR)CEO	I _C =-0.05A, I _B =0	-120	-	-	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} =-5V, I _C =-1A	55	-	240	
	h _{FE} (2)	V _{CE} =-5V, I _C =-4A	30	-	-	
Collector Emitter Saturation Voltage	V _{CE(sat)}	I _C =-4A, I _B =-0.4A	-	-1.0	-2.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} =-5V, I _C =-4A	-	-1.5	-2.5	V
Transition Frequency	f _T	V _{CE} =-10V, I _C =-1A	-	90	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz	-	150	-	pF

Note: hFE(1) Classification. R:55~110, O:80~160, Y:120~240

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COMMON EMITTER
 $V_{CE} = -10V$
 $T_c = 25^{\circ}C$

TRANSITION FREQUENCY f_T (MHz)

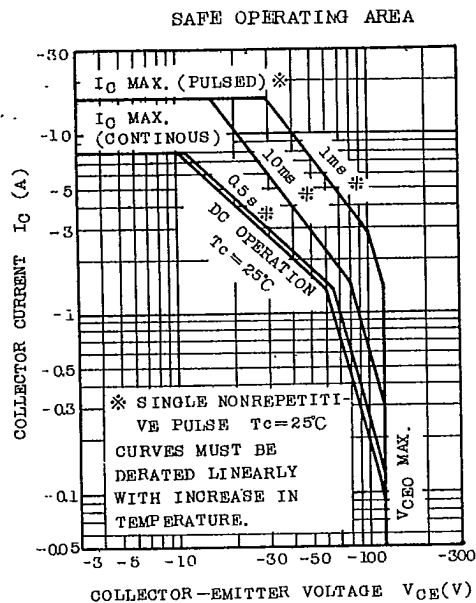
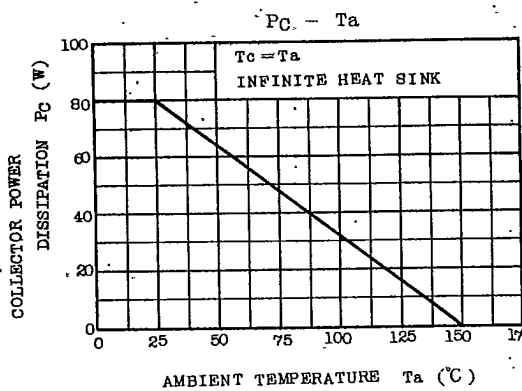
COLLECTOR CURRENT I_C (A)

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